

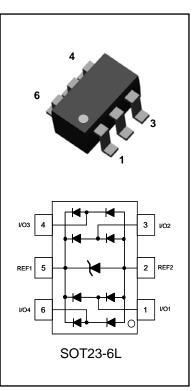


Low Capacitance TVS and Diode Array

This diode array is configured to protect up to four data transmission lines acting as a line terminator, minimizing overshoot and undershoot conditions due to bus impedance as well as protect against over-voltage events as electrostatic discharges. Additionally the TVS Device offers overvoltage transient protection between the operating voltage bus and ground plane.

SPECIFICATION FEATURES

- Peak Power Dissipation of 350W 8/20µs
- Maximum Capacitance of 3.0pF at 0Vdc 1MHz Line-to-Ground
- Maximum Leakage Current of 0.1µA @ VRWM
- Industry Standard SMT Package SOT23-6L
- IEC61000-4-2, IEC61000-4-4 and IEC61000-4-5 Full Compliance
- 100% Tin Matte finish (LEAD-FREE PRODUCT)



APPLICATIONS

- USB 2.0 and Firewire Port Protection
- LAN/WLAN Access Point terminals
- Video Signal line protection
- I²C Bus Protection



MAXIMUM RATINGS Tj = 25°C Unless otherwise noted

Rating	Symbol	Value	Units
Peak Pulse Power (8/20µs Waveform)	P _{PPM}	350	W
Peak Pulse Current (8/20µs Waveform)	۱ _{PP}	17.5	А
Operating Junction Temperature Range	ТJ	-55 to +150	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Soldering Temperature, t max = 10s	ΤL	260	°C





ELECTRICAL CHARACTERISTICS Tj = 25°C unless otherwise noted

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V _{WRM}				5	V
Reverse Breakdown Voltage	V _{BR}	I _{BR} = 1mA	6.2			V
Reverse Leakage Current	۱ _R	$V_R = 5V$			0.1	μA
Clamping Voltage (8/20µs)	Vc	I _{pp} = 1 A			9.5	V
Clamping Voltage (8/20µs)	Vc	Ipp = 10 A			12	V
Clamping Voltage (8/20µs)	Vc	I _{pp} = 17.5 A			20	V
Off State Junction Capacitance	Cj	0 Vdc Bias f = 1MHz Between I/O pins and GND			3	pF
		0 Vdc Bias f = 1MHz Between I/O pins			2	pF





PACKAGE DIMENSIONS AND SUGGESTED PAD LAYOUT

